

## **KL Pey's research awards**

### **Best papers**

- **Best Paper Award** of 2019 IEEE International Reliability Physics Symposium (IRPS), "[\*Spatio-Temporal Defect Generation Process in Irradiated HfO<sub>2</sub> MOS Stacks: Correlated versus Uncorrelated Mechanisms\*](#)", Fernando Leonel Aguirre, Andrea Padovani, Alok Ranjan, Nagarajan Raghavan, Nahuel Vega, Nahuel Müller, Sebastián Matías Pazos, Mario Debray, Joel Molina, **Kin Leong Pey**, Félix Palumbo.
- **Best Student Paper** of 2018 International Symposium for Testing and Failure Analysis (ISTFA), "[\*Pattern Search Automation for Combinational Logic Analysis\*](#)" (Emerging FA Techniques and Concepts session) by PhD student, Mr. Venkat Ravikumar.
- **The Best of Design in Engineering" award** of 2012 American Society for Engineering Education (ACEE) conference, "[\*A Symphony of Designettes: Exploring the Boundaries of Design Thinking in Engineering Education\*](#)", Kristin L. Wood, Rajesh Elara Mohan, Sawako Kaijima, Stylianos Dritsas, Daniel D. Frey, Christina Kay White, Daniel D. Jensen, Richard H. Crawford, Diana Moreno, and **Kin-Leong Pey**.
- **Best Paper (Reliability) award** of 2011 IEEE 18<sup>th</sup> International Physical and Failure Analysis Symposium (IPFA), "[\*Study of the charge leakage of dual layer Pt metal nanocrystal-based high-k/SiO<sub>2</sub> flash memory cell - a relaxation current point of view\*](#)", Y.N. Chen, **K.L. Pey**, K.E.J. Goh, Z.Z. Lwin, P.K. Singh and S. Mahapatra.
- **Best Paper (Reliability) award** of 2009 IEEE 16<sup>th</sup> International Physical and Failure Analysis Symposium (IPFA), "[\*Can a MOSFET survive from multiple breakdowns?\*](#)", X Li, C.H. Tung and **K.L. Pey**.
- **2009 Electrochemical Society Norman Hackerman Young Author Award** in Solid-State Science & Technology for "[\*Materials and Electrical Characterization of Er\(Si<sub>1-x</sub>Ge<sub>x</sub>\)<sub>2-y</sub> Films Formed on Si<sub>1-x</sub>Ge<sub>x</sub>\(001\) \(x = 0-0.3\) via Rapid Thermal Annealing\*](#)", E.J. Tan, **K.L. Pey**, D.Z. Chi, P.S. Lee and Y. Setiawan and K.M. Hoe, Journal of the Electrochemical Society, 155(1), pp. H26-H30, 2008.
- **Graduate Student Award/Paper of 2003 Material Research Society Spring Meeting** (USA) for "[\*Experimental characterization of the reliability of multi-terminal dual-damascene copper interconnect trees\*](#)", C.L. Gan, C.V. Thompson, **K.L. Pey**, W.K. Choi, C.W. Chang and Q. Guo.
- **Best Paper (Reliability) Award** of 2002 IEEE 9<sup>th</sup> International Physical and Failure Analysis Symposium (IPFA), "[\*Consequence of preferential void formation at the Cu/Si<sub>3</sub>N<sub>4</sub> interface on the multiple failure mechanisms of cu dual-damascene metallization\*](#)", C.L. Gan, F. Wei, C.V. Thompson, **K.L. Pey**, W.K. Choi and B. Yu.

- **Electrochemical Society Norman Hackerman Young Author Awards 2002** for “*Effect of ion implantation on layer inversion of Ni silicided poly-Si*”, P. S. Lee, **K. L. Pey**, D. Mangelinck, J. Ding, D. Z. Chi, T. Osipowicz, J. Y. Dai and L. Chan published in *Journal of Electrochemical Society*, Vol. 149 (9), G505-G509, 2002.

### **Research Awards**

- **TSMC 2010 Outstanding Student Research Award:** Wu Xing on “*Physical Analysis of Breakdown in Advanced High-k Gate Dielectric Using Transmission Electron Microscopy and Atomistic Simulations*”.
- **Top Place in Photo Contest** for “*Art of Failure Analysis*” of 2010 IEEE 17<sup>th</sup> International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA).
- **Japan Society for the Promotion of Science (JSPS), Visiting Professor**, Tokyo Institute of Technology, 2 February – 7 February 2009.
- **8<sup>th</sup> Place in Photo Contest** for “*Art of Failure Analysis*” of 2008 IEEE 15<sup>th</sup> International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA).
- **TSMC 2008 Outstanding Student Research Awards:**
  - A Commendation Prize in Category III: Physics, Chemistry of Material for Nano-Scale Devices by Li Xiang on “*Gate dielectric reliability study using TEM and EELS*”.
  - A Bronze Prize in Category III: Physics, Chemistry of Material for Nano-Scale Devices by Ong Yi Ching on “*Scanning Tunneling Microscopy of the Sc<sub>2</sub>O<sub>3</sub>/La<sub>2</sub>O<sub>3</sub>/SiO<sub>x</sub> Gate Stack – A Nanoscopic Perspective*”.
- **Japan Society for the Promotion of Science (JSPS) 2007 Scientist Exchange Award** for visiting to Tokyo Institute of Technology of Prof. Hiroshi Iwai’s lab.

### **Highlights**

- **Top papers for conference highlights** of 2018 IEEE International Reliability Physics Symposium (IRPS), “*Mechanism of soft and hard breakdown in hexagonal boron nitride 2D dielectrics*”, A. Ranjan, N. Raghavan, S.J.O’ Shea, S. Mei, M. Bosman, K. Shubhakar and **K.L. Pey**.
- **Highlight of the IEEE 2008 Electron Device Meeting (IEDM)**, “*The Chemistry of Gate Dielectric Breakdown*”, X Li, CH Tung, **KL Pey** and V. Lo.

### **Others**

- **2011 Chinese Government Award** for Outstanding Self-financed students abroad for PhD research by Wu Xing.
- **2011 IEEE Electron Devices Society PhD Student Fellowship** for Nagarajan Raghavan.

- **IEEE Electron Devices Society 2002 Graduate Student Fellowship** for PhD student Alfred YF Chong's work on "*Fabrication of ultra-shallow junctions and advanced gate stacks for ULSI technologies using laser thermal processing*".